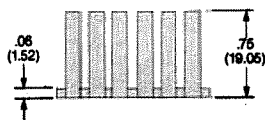
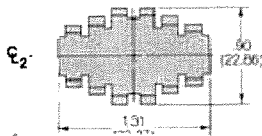


# SECTION 2

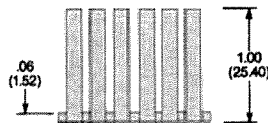
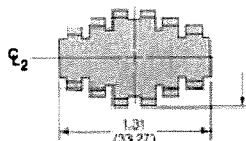
## HEAT DISSIPATORS FOR PLASTIC CASE, CASE-MOUNTED SEMICONDUCTORS

### LA-A3 Series

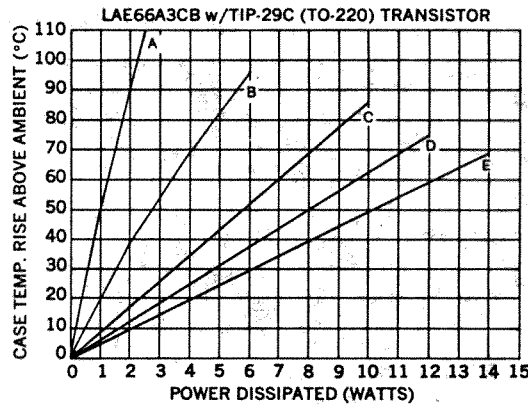


Dimensions are for reference use only. Contact IERC for dimensions with tolerances or standard part drawings.

### LA-A4 Series



Dimensions are for reference use only. Contact IERC for dimensions with tolerances or standard part drawings.



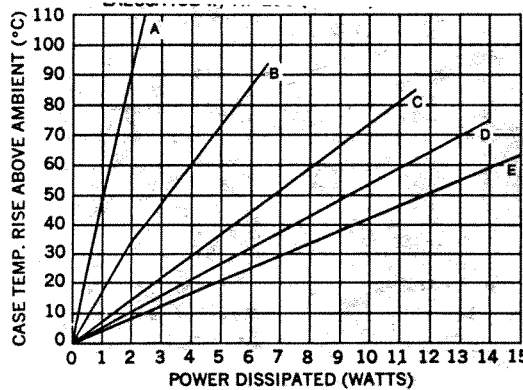
DESCRIPTION OF CURVES  
 A. N.C. Horiz. Device Only Mounted to G-10.  
 B. N.C. Horiz. & Vert. With Dissipator.  
 C. 200 FPM w/Diss.  
 D. 500 FPM w/Diss.  
 E. 1000 FPM w/Diss.

- Thermal Resistance Case to Sink is 0.9-1.1 °C/W w/Joint Compound.
- Derate 0.5 °C/watt for unplated part in natural convection only.
- Derate 3.0 °C/watt for Insulube® part in natural convection only.

### Ordering Information

IERC PART NO.				Semiconductor Accommodated	Hole pat. ref. no. (see pg. 2-27)	Max. Weight (Grams)
Unplated	Comm'l. Black Anodize	Mil. Black Anodize	Insulube® 448			
LA000A3U	LA000A3CB	LA000A3B	LA000A3	Undrilled	—	6.1
LAE66A3U	LAE66A3CB	LAE66A3B	LAE66A3	TO-126, TO-220	1	6.1

Note: See page iv for other finishes.



DESCRIPTION OF CURVES  
 A. N.C. Horiz. Device Only Mounted to G-10.  
 B. N.C. Horiz. & Vert. With Dissipator.  
 C. 200 FPM w/Diss.  
 D. 500 FPM w/Diss.  
 E. 1000 FPM w/Diss.

- Thermal Resistance Case to Sink is 0.9-1.1 °C/W w/Joint Compound.
- Derate 0.6 °C/watt for unplated part in natural convection only.
- Derate 3.0 °C/watt for Insulube® part in natural convection only.

IERC PART NO.				Semiconductor Accommodated	Hole pat. ref. no. (see pg. 2-27)	Max. Weight (Grams)
Unplated	Comm'l. Black Anodize	Mil. Black Anodize	Insulube® 448			
LA000A4U	LA000A4CB	LA000A4B	LA000A4	Undrilled	—	7.6
LAE66A4U	LAE66A4CB	LAE66A4B	LAE66A4	TO-126, TO-220	1	7.6

Note: See page iv for other finishes.